

isc N-Channel MOSFET Transistor
2SK3889L
FEATURES

- Drain Current : $I_D = 9.0A @ T_C = 25^\circ C$
- Drain Source Voltage : $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance : $R_{DS(on)} = 1.0 \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

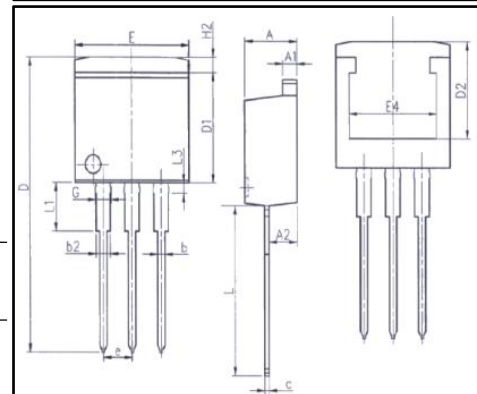
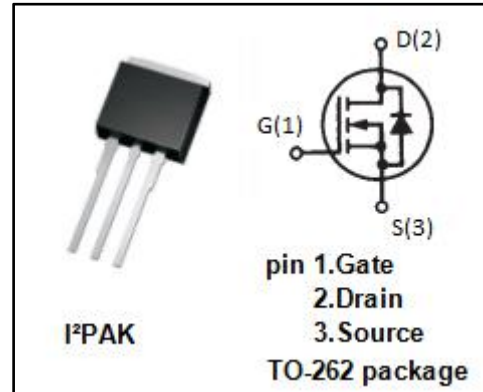
- motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|----------|------------|
| V_{DSS} | Drain-Source Voltage | 600 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 30 | V |
| I_D | Drain Current-Continuous | 9.0 | A |
| I_{DM} | Drain Current-Single Pluse | 36 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 165 | W |
| T_J | Max. Operating Junction Temperature | -55~150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|--------------------------------------|------|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 1.36 | $^\circ C/W$ |



| DIM | MM | |
|-----|---------|-------|
| | MIN | MAX |
| A | 4.37 | 4.77 |
| A1 | 1.22 | 1.42 |
| A2 | 2.47 | 2.87 |
| b | 0.7 | 0.97 |
| b2 | 1.17 | 1.42 |
| c | 0.28 | 0.53 |
| D | 23.2 | 24.02 |
| D1 | 8.38 | 8.9 |
| D2 | 6 | / |
| E | 9.9 | 10.39 |
| E4 | 7.3 | / |
| E | 2.54BSC | |
| G | 1.25 | 1.5 |
| H2 | / | 1.31 |
| L | 13.34 | 14.1 |
| L1 | 3.3 | 4.06 |
| L3 | 0.95 | 1.15 |

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 600 | -- | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = 10V; I _D = 0.25mA | 3.0 | 5.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 4.5A | -- | 1.0 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V; V _{DS} = 0 | -- | ±0.1 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 600V; V _{GS} = 0 | -- | 25 | uA |
| V _{SD} | Forward On-Voltage | I _S = 9A; V _{GS} = 0 | -- | 1.5 | V |

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